


SGS-THOMSON
 MICROELECTRONICS

STH26N25
STH26N25FI

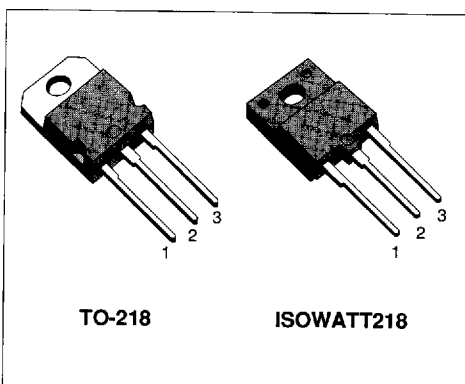
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V _{DSS}	R _{DS(on)}	I _D
STH26N25	250 V	< 0.11 Ω	26 A
STH26N25FI	250 V	< 0.11 Ω	16 A

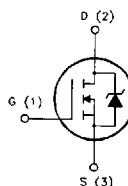
- TYPICAL R_{DS(on)} = 0.085 Ω
- AVALANCHE RUGGEDNESS TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- MOTOR CONTROL, AUDIO AMPLIFIERS
- INDUSTRIAL ACTUATORS
- DC-DC & DC-AC CONVERTERS FOR TELECOM, INDUSTRIAL AND CONSUMER ENVIRONMENT



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STH26N25	STH26N25FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	250		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	250		V
V _{GS}	Gate-source Voltage	± 20		V
I _D	Drain Current (continuous) at T _c = 25 °C	26	16	A
I _o	Drain Current (continuous) at T _c = 100 °C	16	10	A
I _{DM} (*)	Drain Current (pulsed)	104	104	A
P _{tot}	Total Dissipation at T _c = 25 °C	180	70	W
	Derating Factor	1.44	0.56	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T _{slg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(*) Pulse width limited by safe operating area

THERMAL DATA

			TO-218	ISOWATT218	
R _{thj-case}	Thermal Resistance Junction-case	Max	0.69	1.79	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30		°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	0.1		°C/W
T _I	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	26	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 25\text{ V}$)	160	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	40	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100^{\circ}\text{C}$, pulse width limited by T_j max, $\delta < 1\%$)	16	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ $V_{GS} = 0$	250			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125^{\circ}\text{C}$			250 1000	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{ V}$ $I_D = 13\text{ A}$ $V_{GS} = 10\text{ V}$ $I_D = 13\text{ A}$ $T_c = 100^{\circ}\text{C}$		0.085	0.11 0.22	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10\text{ V}$	26			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 13\text{ A}$	9	18		S
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$ $V_{GS} = 0$		2900	3800	pF
C_{oss}	Output Capacitance			600	800	pF
C_{rss}	Reverse Transfer Capacitance			180	250	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 125\text{ V}$ $I_D = 13\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		25 80	35 120	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 200\text{ V}$ $I_D = 26\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		200		A/ μ s
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 200\text{ V}$ $I_D = 26\text{ A}$ $V_{GS} = 10\text{ V}$		125 15 65	180	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 200\text{ V}$ $I_D = 26\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		170 80 260	250 120 380	ns ns ns

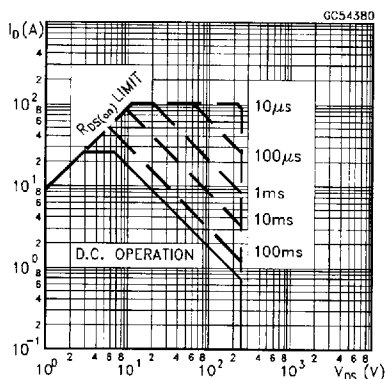
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				26 104	A A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 26\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 26\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$ $T_J = 150^\circ\text{C}$ (see test circuit, figure 5)		400 5.2 26		ns μC A

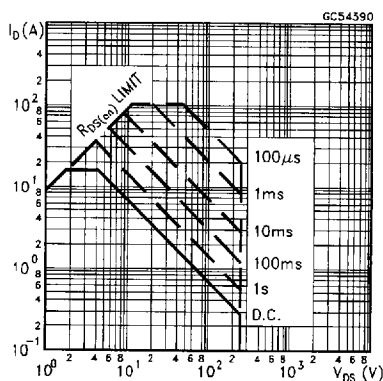
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(*) Pulse width limited by safe operating area

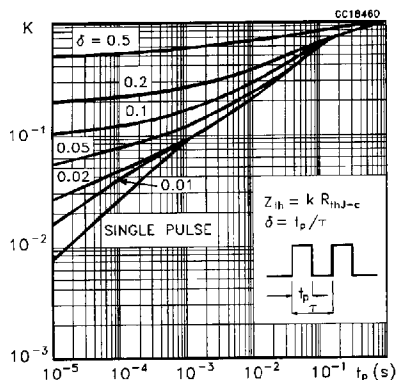
Safe Operating Areas For TO-218



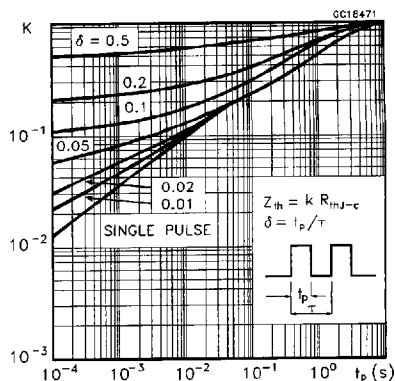
Safe Operating Areas For ISOWATT218



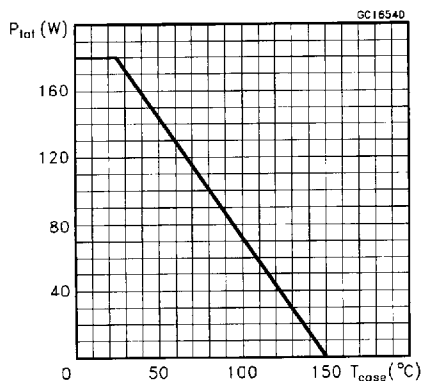
Thermal Impedance For TO-218



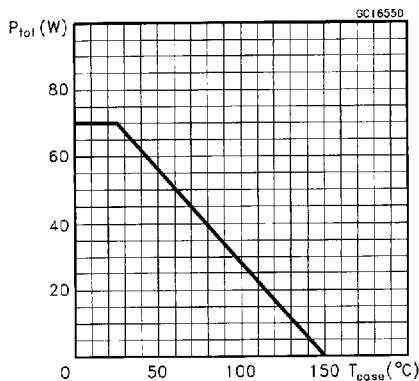
Thermal Impedance For ISOWATT218



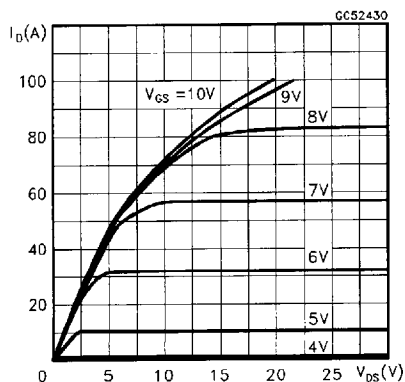
Derating Curve For TO-218



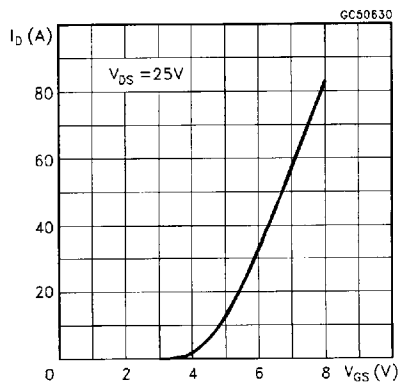
Derating Curve For ISOWATT218



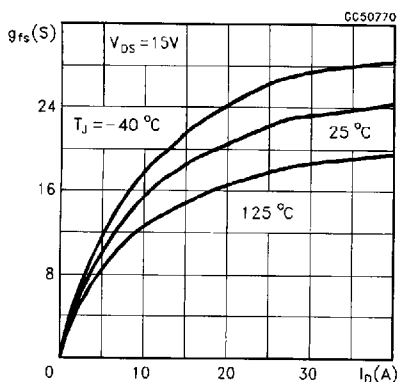
Output Characteristics



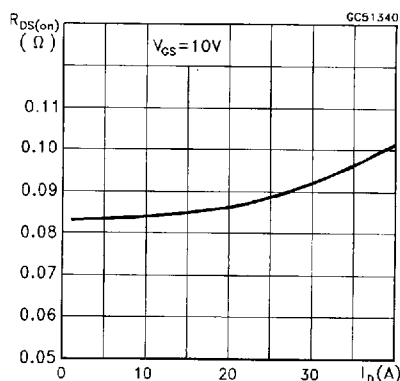
Transfer Characteristics



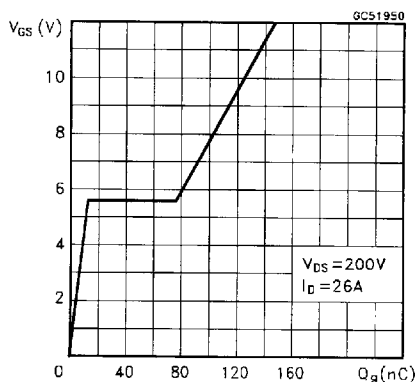
Transconductance



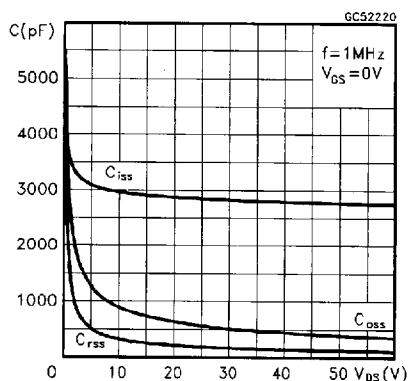
Static Drain-source On Resistance



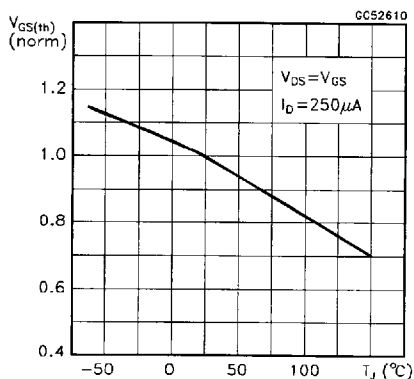
Gate Charge vs Gate-source Voltage



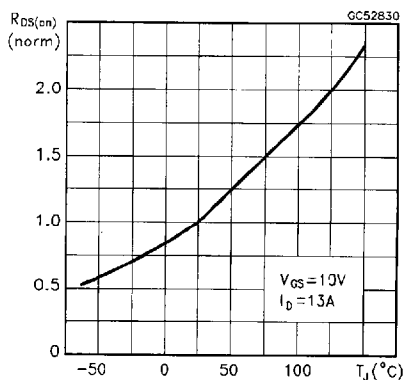
Capacitance Variations



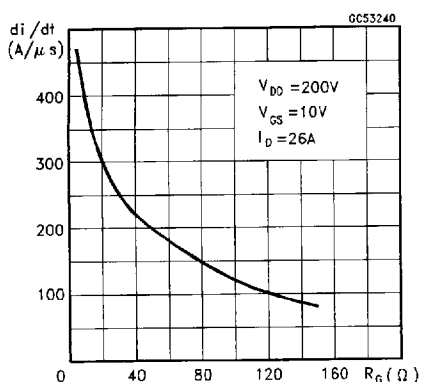
Normalized Gate Threshold Voltage vs Temperature



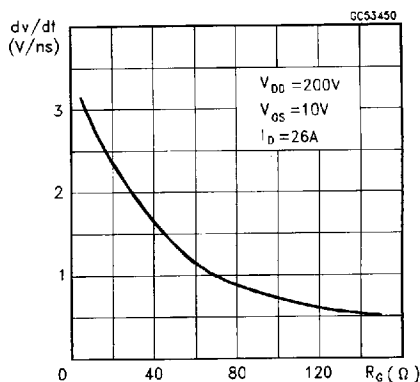
Normalized On Resistance vs Temperature



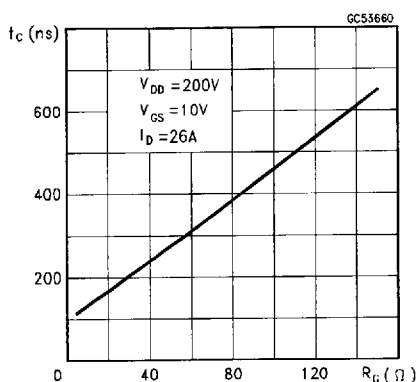
Turn-on Current Slope



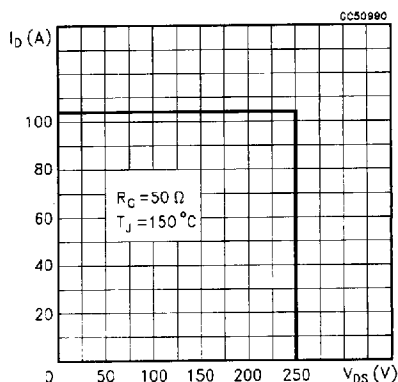
Turn-off Drain-source Voltage Slope



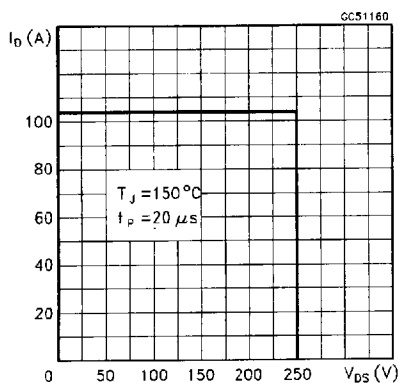
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

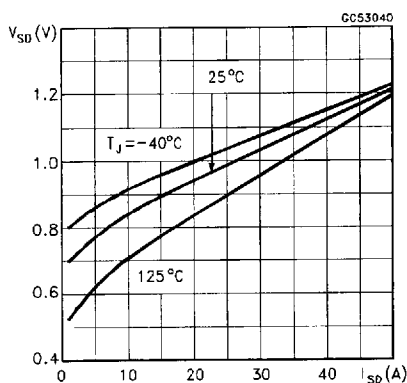
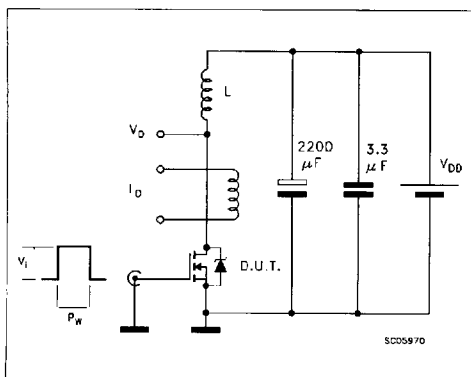
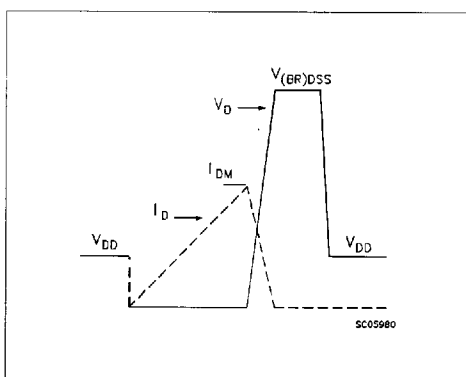
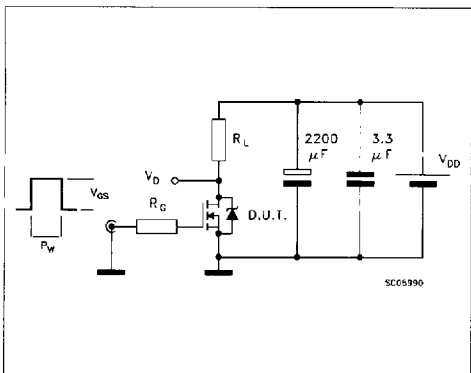
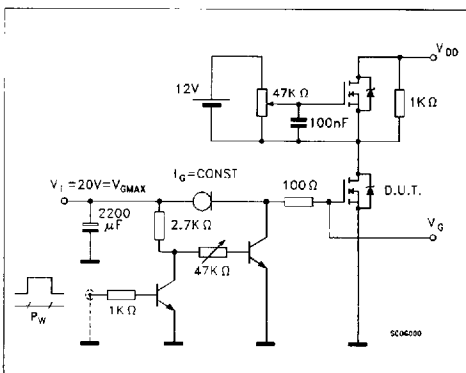


Fig. 1: Unclamped Inductive Load Test Circuits**Fig. 2: Unclamped Inductive Waveforms****Fig. 3: Switching Times Test Circuits For Resistive Load****Fig. 4: Gate Charge Test Circuit****Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time**